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Roll No. : .....

**328654(28)**

**B. E. (Sixth Semester) Examination April-May 2021**

**(New Scheme)**

**(Et&T Branch)**

**VLSI DESIGN**

***Time Allowed : Three hours***

***Maximum Marks : 80***

***Minimum Pass Marks : 28***

***Note : Attempt all questions. Part (a) of each question is compulsory, which is of 2 marks. Attempt any two parts from (b), (c) and (d) each is of 7 marks. Assume suitable data wherever necessary. Draw the diagram to support your answer if required.***

**Unit-I**

1. (a) What is Moore's law?

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- (b) Consider an n-channel MOS system that is characterized by  $x_{ox} = 100 \text{ \AA}$  and  $N_a = 10^{15}/\text{cm}^3$ . An n-type poly gate is used with  $N_{d, poly} = 10^{19}/\text{cm}^3$ . The fixed oxide charge is approximated as  $Q_f = q (10^{11}) \text{ c/cm}^2$  and is the dominant oxide charge term, and the acceptor ion implant dose is assumed to be  $D_i \approx 2 \times 10^{12} /\text{cm}^2$ . Determine the threshold voltage. 7
- (c) Explain the term switching intervals and derive an expression for fall time ( $t_f$ ) in CMOS inverters. 7
- (d) Draw the complete VLSI Design flow for programmable logic devices and Application Specific Integrated Circuits (ASIC). 7

### Unit-II

2. (a) Write the significance of Euler graph to draw stick diagram or layout for any complex logic circuit. 2
- (b) Describe photolithography process for VLSI circuits and role of positive & negative photoresist to draw various patterns. 7

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- (c) Explain the basic sequence of processes to fabricate n-well CMOS inverter. 7
- (d) Write the MOSIS Lamda ( $\lambda$ ) based layout design rules for active area, polysilicon, metal and contacts. 7

### Unit-III

3. (a) Write the difference between stick diagram & layout representation of the circuit. 2
- (b) Draw the pass transistor based circuit diagram & layout for 4 : 1 multiplexer. 7
- (c) Draw the circuit diagram for 6 T SRAM & explain the read and write operations. 7
- (d) Draw the CMOS layout of J-K flip-flop. 7

### Unit-IV

4. (a) Write the critical difference between Concurrent & Sequential Assignment Statements. 2
- (b) Consider the function  $f(x_1, x_2, x_3) = \sum m$

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- (2, 3, 4, 6, 7). Show how it can be realized using 2, two input LUT's only. 7
- (c) With the use of Generate syntax, write the VHDL code to design 16 : 1 multiplexer using 4 : 1 multiplexer as a component. 7
- (d) Explain process statements of VHDL, including general syntax of process, sensitivity list, process declarative items, sequential statements and example. 7

#### Unit-V

5. (a) Define the term test vectors in test bench source code. 2
- (b) Write a VHDL code of Moore type FSM (Finite State Machine) for serial adder. 7
- (c) Write a VHDL code to design Mealy FSM (Finite State Machine) to detect a bit sequence 101. 7
- (d) Write a VHDL code which describes a simple test bench for half adder. 7